

GR-04E001GJ: E-mode GaN Power Transistor

Description

GR-04E001GJ is an enhancement mode GaN on Silicon power transistor. 04E001GJ provides, high current and high operating speed which is suitable for DC to DC power supply applications.

Key Specifications

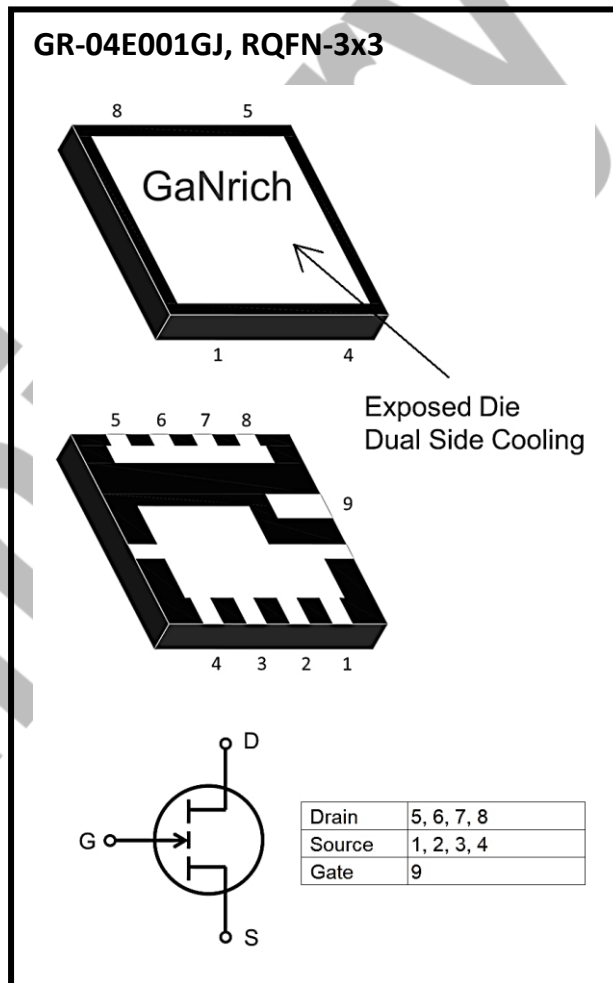
Part Number	GR-04E001GJ
V_{DS} , min.	40V
I_{DS} , Pulse (25°C, TPULSE = 300 μ s)	390A
$R_{DS(ON)}$, typ. @Vgs=5V	1.0m Ω
Q_G , typ.	16.0nC

Features

- 40V enhancement mode power transistor
- $R_{DS(on)}$ = Typ. 1.0m Ω
- Low Q_g for High operating frequency
- Zero reverse recovery

Applications

- High-Efficiency Synchronous Rectification (AC-DC/DC-DC)
- High-Frequency Multi-Topology DC-DC Converters
- High-Power Density DC-DC Power Modules
- Industrial & Automotive Motor Drives



1. Electrical Characteristics

➤ **Table 1 Absolute maximum ratings**

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	40	V
$V_{(TR)DS}$	Transient drain to source voltage ^a	48	V
V_{GS}	Gate- source voltage	-6V ~ +6V	V
I_D	Drain current (continuous) at $T_C = 25^\circ\text{C}$ operation	95.0	A
	Drain current (continuous) at $T_C = 100^\circ\text{C}$ operation	65.5	A
$I_{D,Pulse}$	Pulsed drain current (pulse width: 300 μs , $V_{GS}=5\text{V}$) ^b	390	A
T_J	Operating temperature	-40 to +150	$^\circ\text{C}$
T_S	Storage temperature	-40 to +150	$^\circ\text{C}$
MSL	Moisture sensitivity level	MSL3	-

a. In off-state, spike duty cycle $D < 0.01$, spike duration $< 1\mu\text{s}$

b. Defined by product design and characterization. Value is not tested to full current in production

➤ **Table 2 Thermal Characteristics**

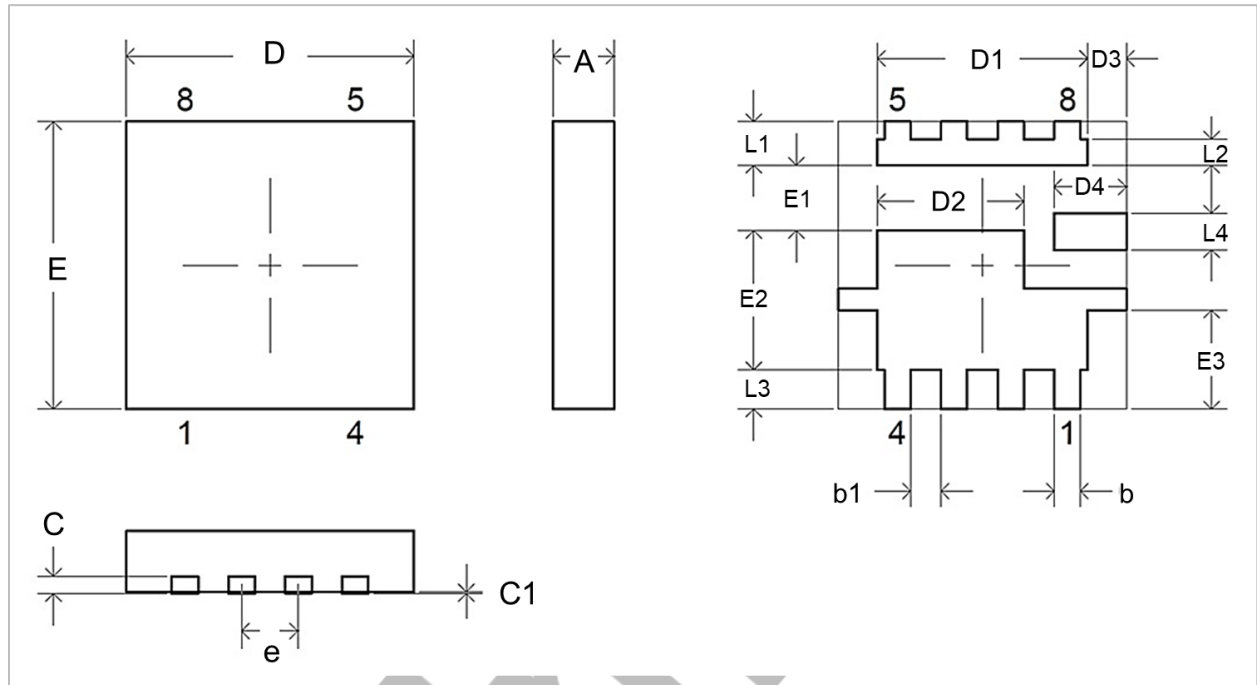
Symbol	Parameter	Value	Unit
$R_{\theta JC_Top}$	Thermal resistance junction-case, Top	0.65	$^\circ\text{C}/\text{W}$
$R_{\theta JC_Bot}$	Thermal resistance junction-case, Bottom	1.25	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal resistance junction-ambient	60.0	$^\circ\text{C}/\text{W}$

a. Tested in package DFN 3x3.

➤ **Table 3** Electrical Characteristics ($T_{CASE} = 25\text{ }^{\circ}\text{C}$ unless otherwise stated)

Symbol	Parameter	Conditions	Values			Unit
			min.	typ.	max.	
V_{DSS}	Drain-source voltage	$V_{GS} = 0V, I_D = 150\mu A$	40	-	-	V
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 15mA$	0.8	1.2	1.8	V
$R_{DS(on)}$	Drain-source on-resistance	$V_{GS} = 5V, I_D = 30A$	-	1.0	1.2	$m\Omega$
I_{DSS}	Drain-source leakage current	$V_{DS} = 32V, V_{GS} = 0V$	-	10	800	μA
I_{GSS}	Gate-to-Source Forward Leakage current	$V_{GS} = +5V$	-	0.28	56	mA
	Gate-to-Source Forward Leakage current	$V_{GS} = +5V, T_J = 125^{\circ}\text{C}$	-	1.25	37.5	mA
	Gate-to-Source Reverse Leakage current	$V_{GS} = -4V$	-	0.23	6.9	mA
C_{ISS}	Input capacitance	$V_{DS} = 20V, V_{GS} = 0V$	-	2350	-	pF
C_{OSS}	Output capacitance		-	1250	-	
C_{RSS}	Reverse transfer capacitance		-	27	-	
Q_G	Gate charge	$V_{DS} = 20V, V_{GS} = 5V, I_D = 30A$	-	16.0	-	nC
Q_{GS}	Gate-source charge	$V_{DS} = 20V, I_D = 30A$	-	4.0	-	
Q_{GD}	Gate-drain charge		-	3.6	-	
Q_{OSS}	Output charge	$V_{DS} = 20V, V_{GS} = 0V$	-	25	-	
Q_{RR}	Source-Drain Recovery Charge	-	-	0	-	

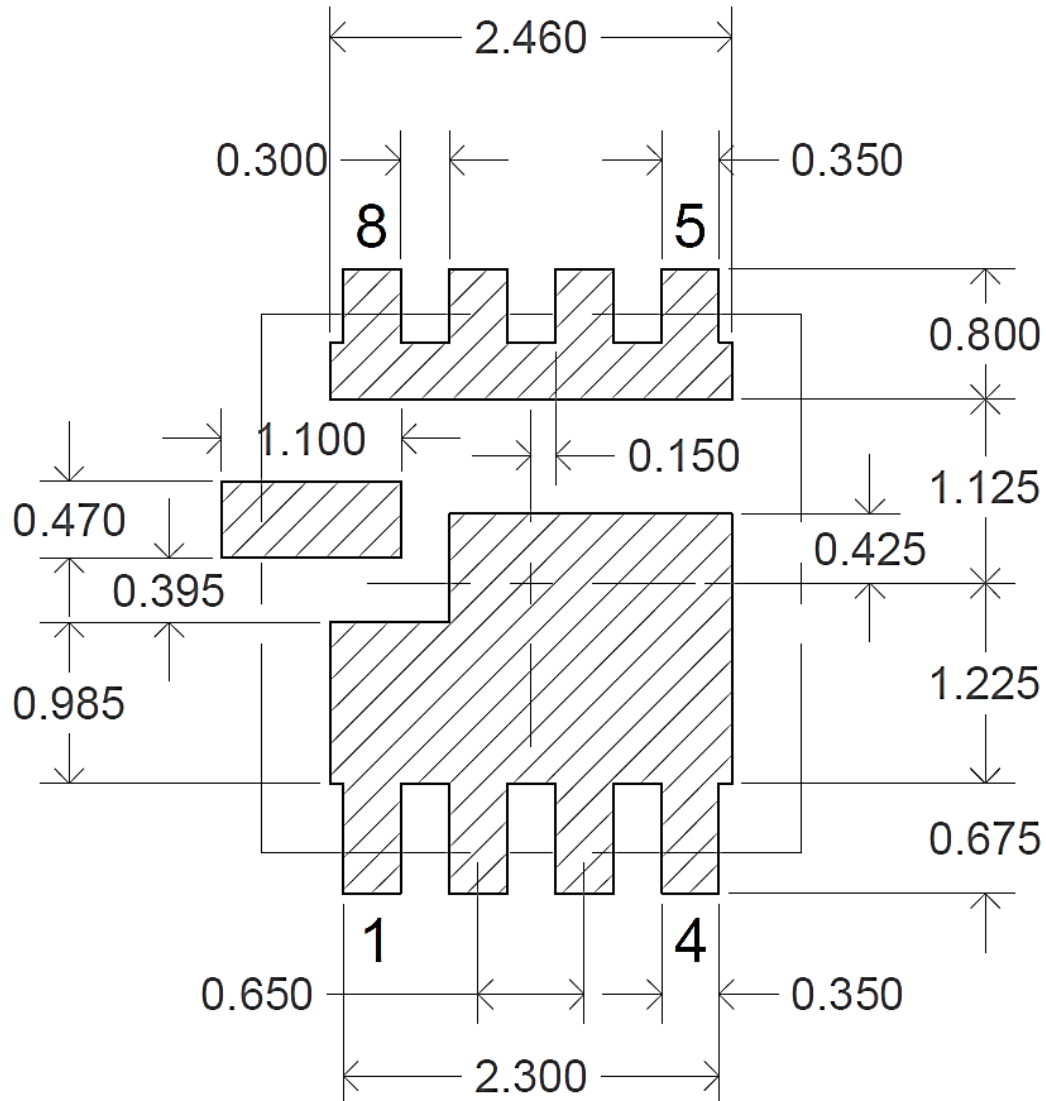
2. Package Outline Dimensions



➤ Table 4 Dimension of GR-RQFN-3x3

SYMBOL	DIMENSION (IN MM)			SYMBOL	DIMENSION (IN MM)		
	MIN.	NOM.	MAX.		MIN.	NOM.	MAX.
A	---	---	0.70	D3	0.345	0.445	0.545
C	0.203 REF			D4	0.73	0.83	0.93
C1	---	---	0.05	E1	0.65	0.75	0.85
D	3.20	3.30	3.40	E2	1.50	1.60	1.70
E	3.20	3.30	3.40	E3	1.035	1.135	1.235
e	0.65 BSC			L1	0.40	0.50	0.60
b	0.20	0.30	0.40	L2	0.20	0.30	0.40
b1	0.25	0.35	0.45	L3	0.35	0.45	0.55
D1	2.31	2.41	2.51	L4	0.32	0.42	0.52
D2	1.58	1.68	1.78	---	---	---	---

3. Recommended PCB footprint (Unit: mm)



*All dimensions are in units mm

*Not to Scale

4. Change Log

Version	Date	Description
0.1	January 12, 2026	Initial version
0.2	April 16, 2026	Electrical characteristics revised

- **Note:** GaNrich semiconductor reserves the right to revise products and/or specifications without notice.